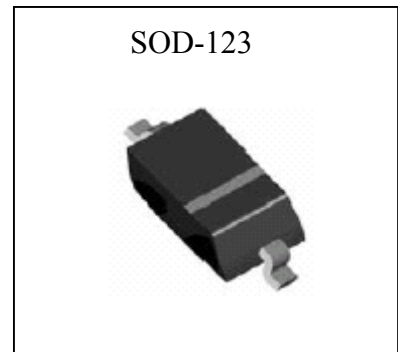


Fast Switching Diodes

BAS21SH


Features

- Fast switching speed
- Low forward voltage drop
- Pb-free lead plating package

Mechanical Data

- Case: Molded plastic, JEDEC SOD-123.
- Terminals: Pure tin plated, solderable per MIL-STD-202 method 208
- Polarity: Indicated by cathode band.
- Weight: 0.01 gram approximately

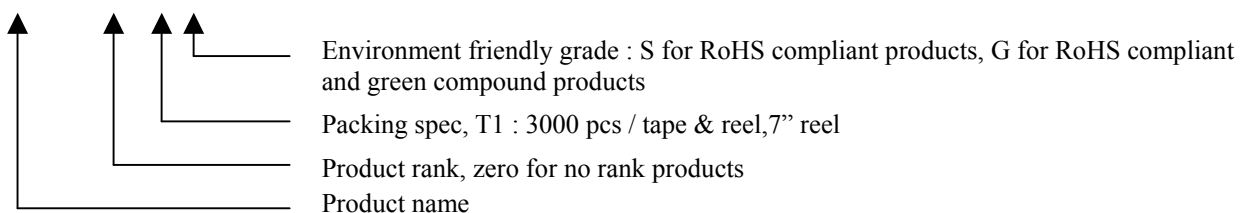
Maximum Ratings and Electrical Characteristics

(Rating at 25°C ambient temperature unless otherwise specified.)

Parameter	Symbol	Type	Units
Non-repetitive peak reverse voltage	V_{RM}	250	V
Repetitive peak reverse voltage	V_{RRM}	250	
Working peak reverse voltage	V_{RWM}	250	
RMS voltage	V_{RMS}	141	
DC blocking voltage	V_R	250	
Forward continuous current	I_{FM}	400	mA
Average rectified output current	I_O	200	
Peak forward surge current @	I_{FSM}	$t=1ms$	A
		$t=1s$	
Repetitive peak forward current	I_{FRM}	625	mA
Power dissipation	P_D	500	mW
Thermal resistance, Junction to ambient	$R_{\theta JA}$	250	°C/W
Operating and storage temperature range	$T_J; T_{STG}$	-65 ~ +150	°C

Ordering Information

Device	Package	Shipping
BAS21SH-0-T1-G	SOD-123 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel



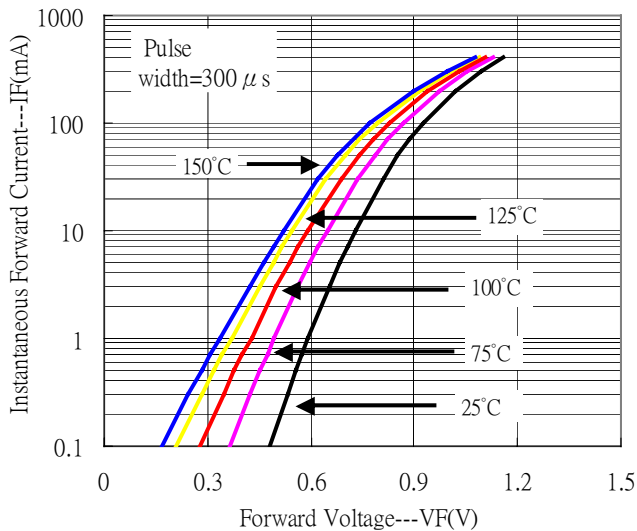


Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

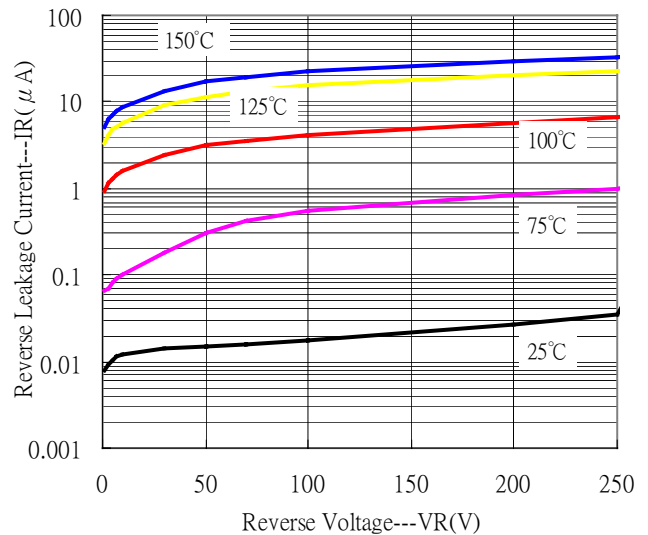
Parameters	Symbol	Conditions	Min	Typ.	Max	Unit
Forward voltage	V_F	$I_F=100\text{mA}$ $I_F=200\text{mA}$	-	-	1 1.25	V
Reverse current	I_R	$V_R=200\text{V}$	-	-	100	nA
Junction Capacitance	C_J	$V_R=0\text{V}$, $f=1\text{MHz}$	-	-	5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=30\text{mA}$, $I_{rr}=0.1 \times I_R$, $R_L=100\Omega$	-	-	50	ns

Typical Characteristics

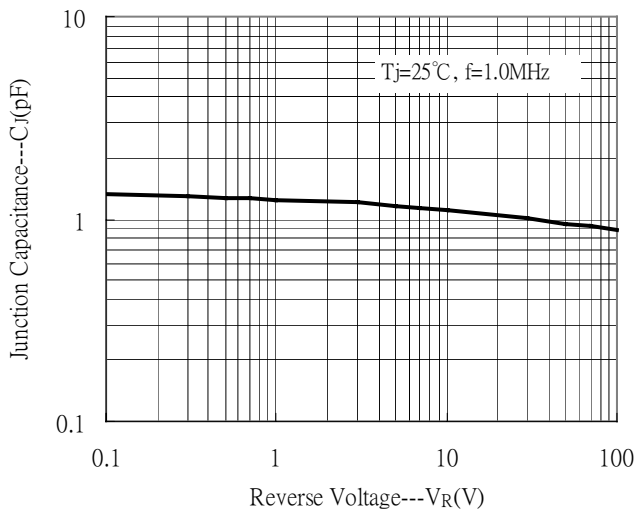
Forward Current vs Forward Voltage



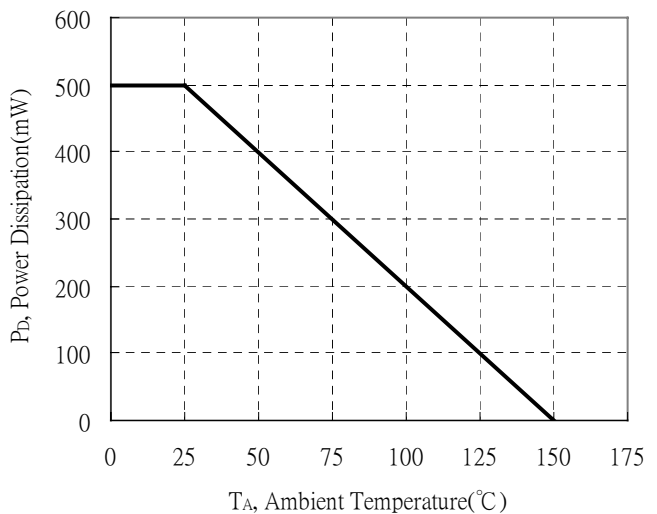
Reverse Leakage Current vs Reverse Voltage



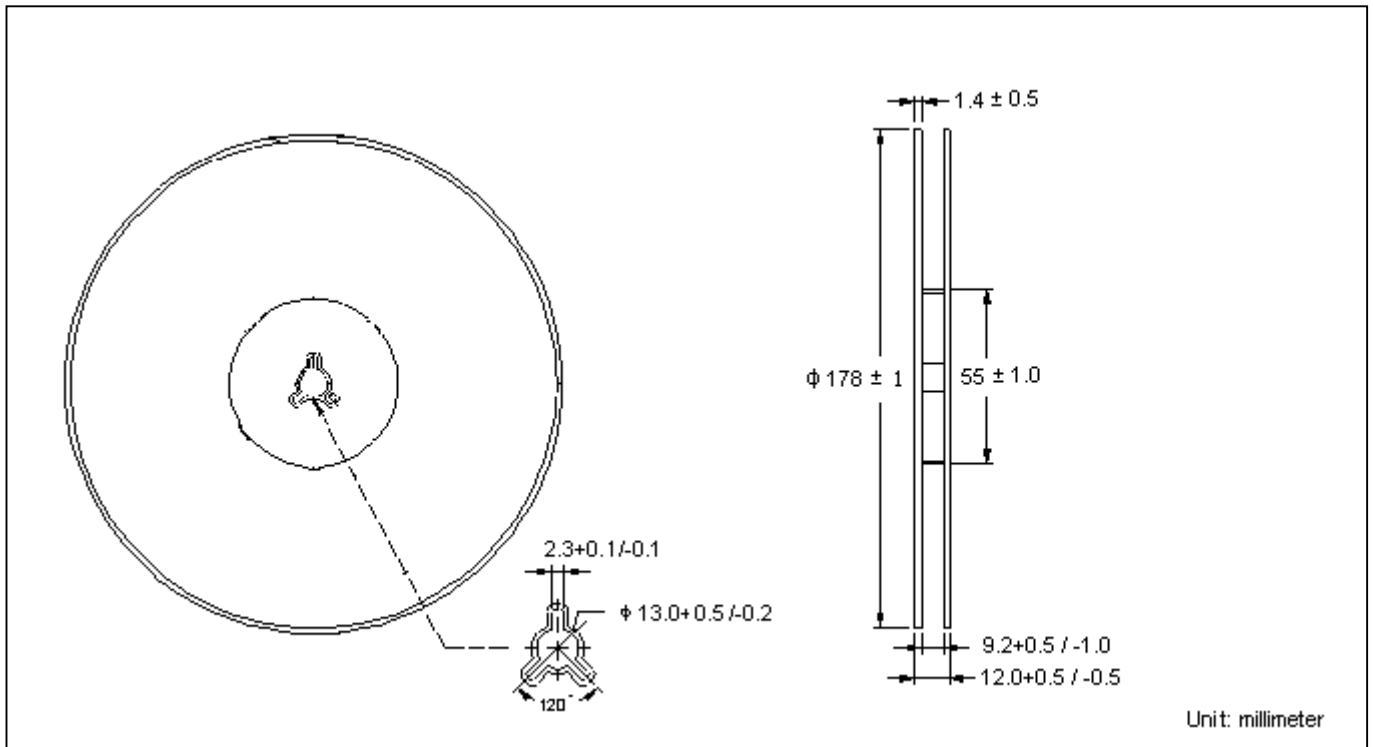
Junction Capacitance vs Reverse Voltage



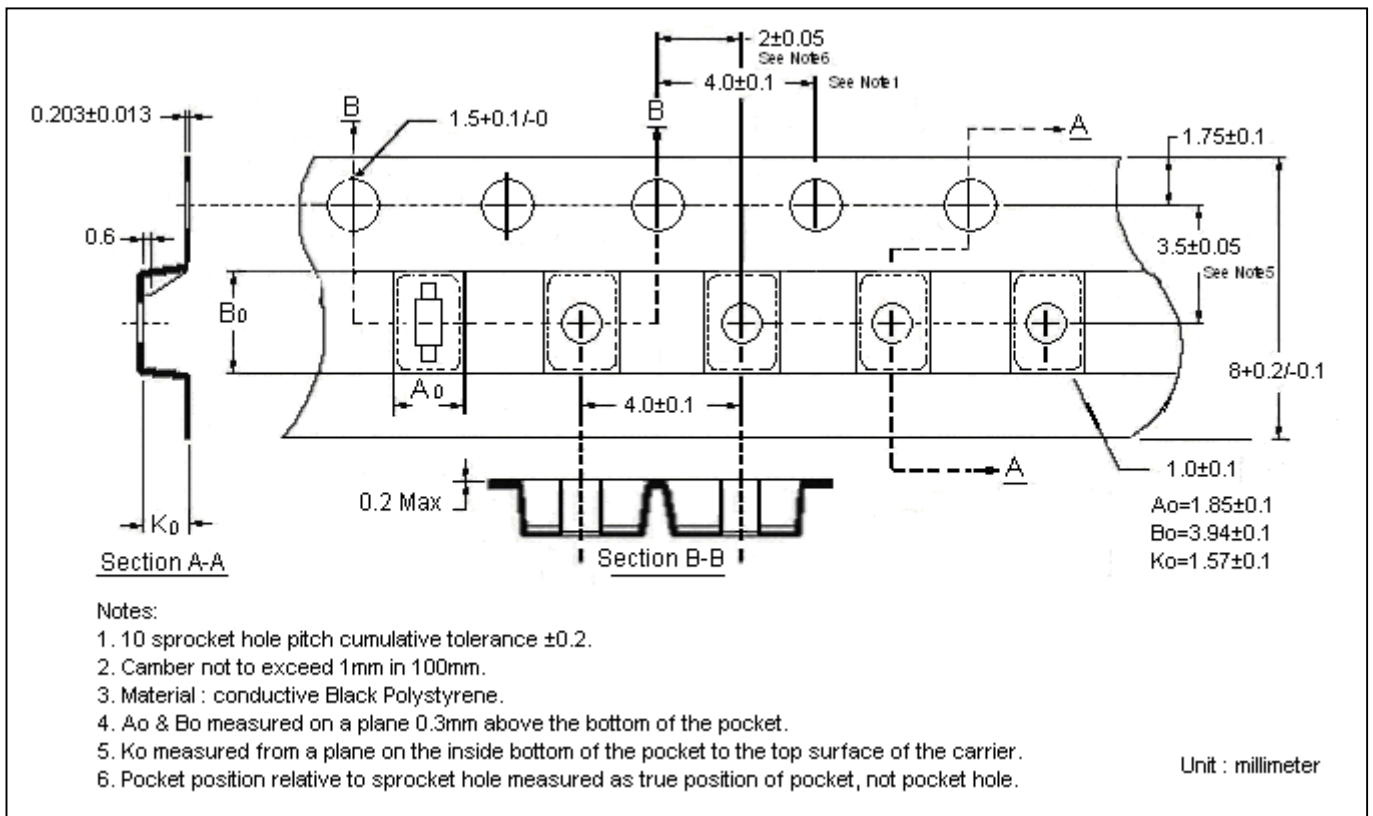
Power Derating Curve



Reel Dimension

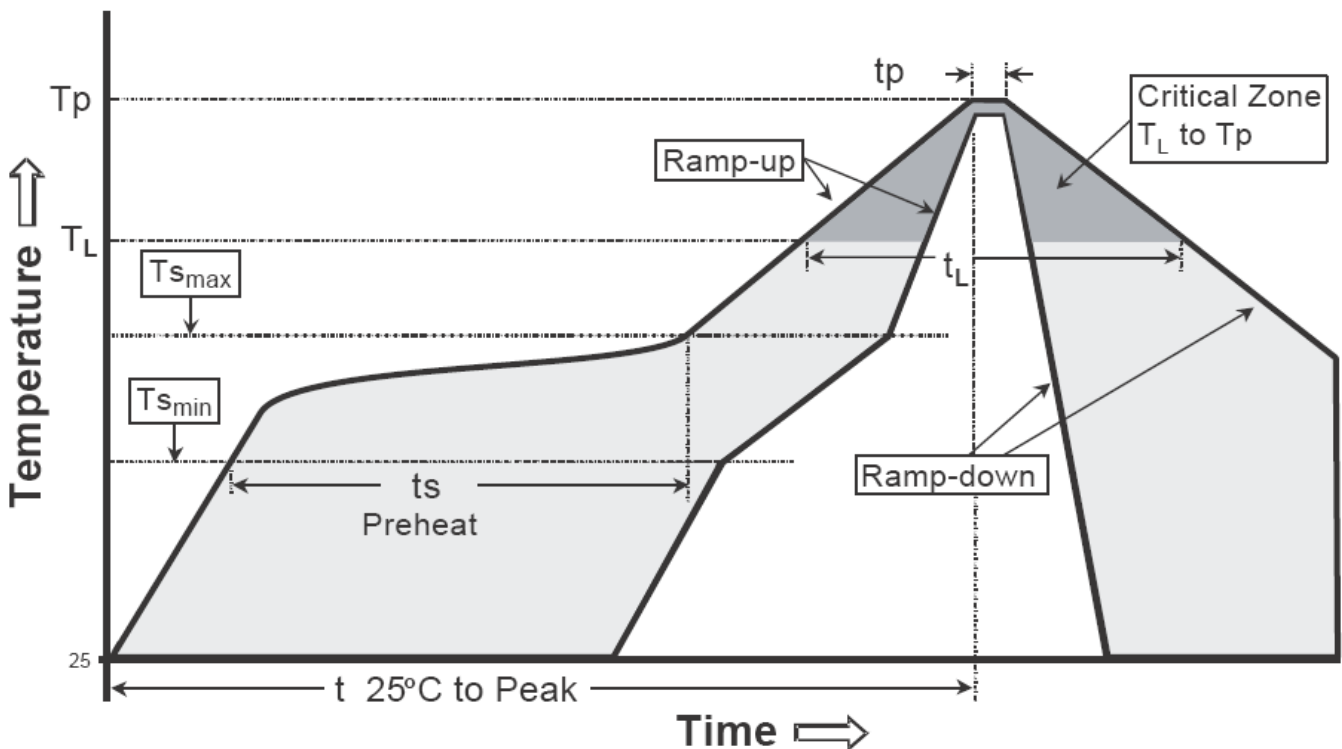


Carrier Tape Dimension



Recommended wave soldering condition

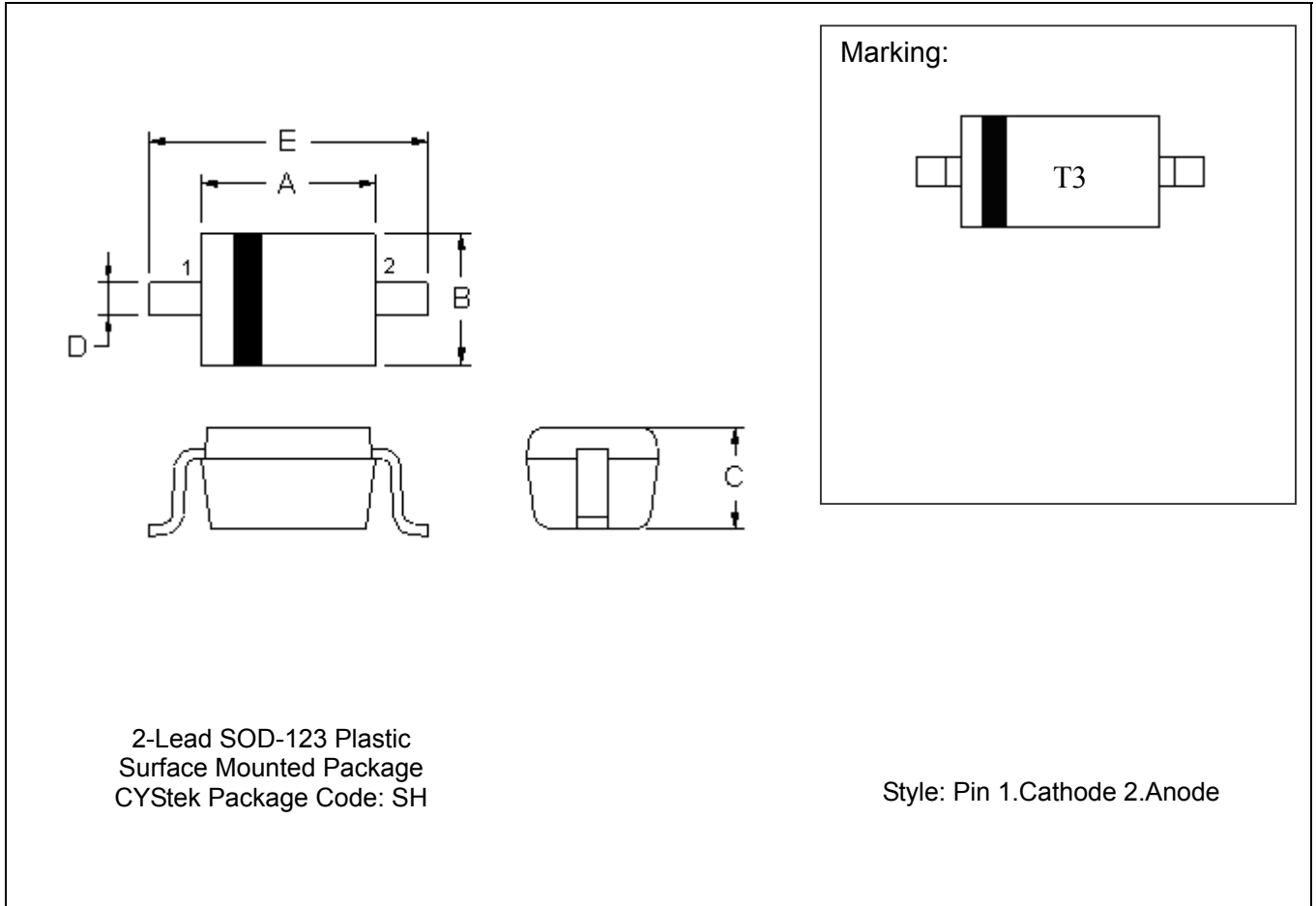
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(t _p)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOD-123 Dimension



2-Lead SOD-123 Plastic
 Surface Mounted Package
 CYStek Package Code: SH

Style: Pin 1.Cathode 2.Anode

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.102	0.110	2.600	2.800	D	0.018	0.026	0.450	0.650
B	0.059	0.067	1.500	1.700	E	0.140	0.152	3.550	3.850
C	0.041	0.049	1.050	1.250					

Notes: 1.Controlling dimension : millimeters.
 2.Lead thickness specified per L/F drawing with solder plating.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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